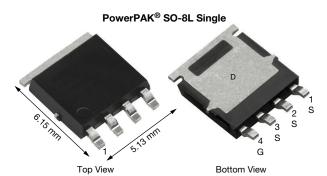


N-Channel 45 V (D-S) MOSFET

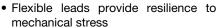


PRODUCT SUMMARY						
V _{DS} (V)	45					
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.0019					
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.00265					
Q _g typ. (nC)	34					
I _D (A) ^a	113					
Configuration	Single					

ORDERING INFORMATION

FEATURES

- TrenchFET® Gen IV power MOSFET
- Very low Q_q and Q_{oss} reduce power loss and improve efficiency

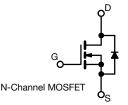




- 100 % R_a and UIS tested
- Q_{gd}/Q_{gs} ratio < 1 optimizes switching characteristics
- · Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

APPLICATIONS

- · Synchronous rectification
- High power density DC/DC
- DC/AC inverters



Package	PowerPAK SO-8L				
Lead (Pb)-free and halogen-free	SIJ450DP-T1-GE3				
ABSOLUTE MAXIMUM RATINGS	(T _A = 25 °C, unles	s otherwise noted)			
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	45	V	
Gate-source voltage		V_{GS}	+20, -16	v	
	T _C = 25 °C		113		
Continuous drain current (T = 150 °C)	T _C = 70 °C		91		
Continuous drain current (1) = 150 Ci					

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage Gate-source voltage		V _{DS}	45	V	
		V _{GS}	+20, -16	V	
	T _C = 25 °C		113		
Continuous drain surrent (T = 150 °C)	T _C = 70 °C		91		
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	I _D	36 ^{b, c}		
	T _A = 70 °C		28.7 b, c	Α	
Pulsed drain current (t = 100 μs)		I _{DM}	300	A	
Continuous source-drain diode current	T _C = 25 °C	,	43.6		
	T _A = 25 °C	I _S	4.3 b, c		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	40		
Single pulse avalanche energy	L = 0.1 MH	E _{AS}	80	mJ	
	T _C = 25 °C		48	w	
Maximum power dissipation	T _C = 70 °C		30.7		
	T _A = 25 °C	P _D	4.8 b, c		
	T _A = 70 °C		3.0 b, c		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	- °C	
Soldering recommendations (peak temperature) d, e			260		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient b, f	t ≤ 10 s	R_{thJA}	22	26	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	1.7	2.6	0/00

Notes

- a. $T_C = 25 \,^{\circ}C$
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 10 s
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 70 °C/W



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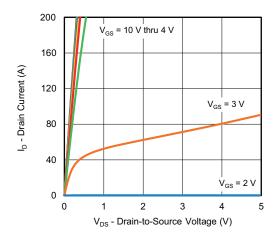
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static			<u> </u>	<u> </u>		
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_{D} = 1 \text{ mA}$	45	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	$I_D = 1 \text{ mA}$	-	30	-	1.1/0
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-5.6	-	mV/°
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0	-	2.3	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = +20, -16 \text{ V}$	-	-	± 100	nA
Zana anta calta na disaisa accument	,	V _{DS} = 45 V, V _{GS} = 0 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 45 V, V _{GS} = 0 V, T _J = 75 °C	-	-	20	μA
On-state drain current a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	50	-	-	Α
Drain acuras an atata registance 8	В	V _{GS} = 10 V, I _D = 10 A	-	0.00155	0.0019	0
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$	-	0.0021	0.00265	Ω
Forward transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_{D} = 10 \text{ A}$	-	105	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	5920	-	
Output capacitance	C _{oss}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	805	-	pF
Reverse transfer capacitance	C _{rss}		-	53	-	
Tatal mate about	0	V _{DS} = 20 V, V _{GS} = 10 V, I _D = 10 A	-	75.5	114	
Total gate charge	Q _g		-	34	51	
Gate-source charge	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$	-	17	-	nC
Gate-drain charge	Q _{gd}		-	4.5	-	
Output charge	Q _{oss}	V _{DS} = 20 V, V _{GS} = 0 V	-	40.5	-	
Gate resistance	R _g	f = 1 MHz	0.5	1.2	2	Ω
Turn-on delay time	t _{d(on)}		-	15	30	
Rise time	t _r	V_{DD} = 20 V, R_L = 2 Ω	-	6	12	
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	41	82	-
Fall time	t _f		-	6	12	
Turn-on delay time	t _{d(on)}		-	36	72	ns
Rise time	t _r	$V_{DD} = 20 \text{ V}, R_L = 2 \Omega$	-	70	140	
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	41	82	
Fall time	t _f		-	8	16	
Drain-Source Body Diode Characteristic	s					
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	43.6	^
Pulse diode forward current ($t_p = 100 \mu s$)	I _{SM}		-	-	300	Α
Body diode voltage	V_{SD}	I _S = 5 A	-	0.71	1.1	V
Body diode reverse recovery time	t _{rr}		-	40	80	ns
Body diode reverse recovery charge	Q _{rr}	$I_F = 10 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	47	94	nC
Reverse recovery fall time	ta	T _J = 25 °C	-	27	-	_
Reverse recovery rise time	t _b		-	13	-	ns

Notes

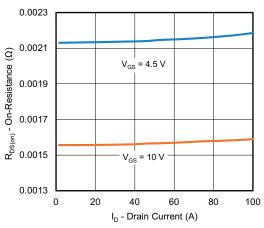
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

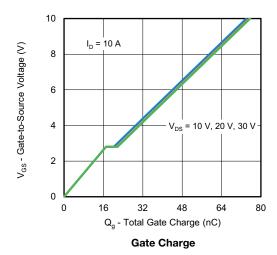


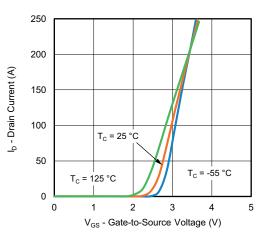


Output Characteristics

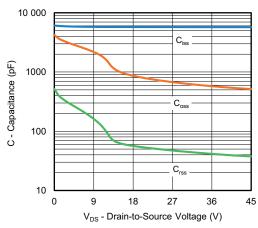


On-Resistance vs. Drain Current

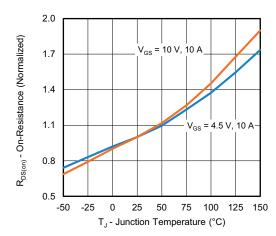




Transfer Characteristics

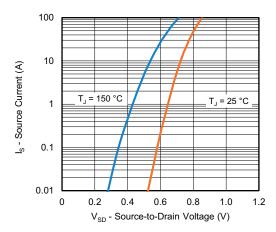


Capacitance

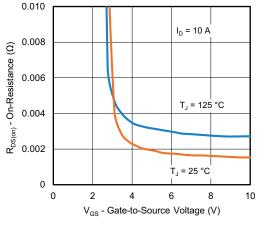


On-Resistance vs. Junction Temperature

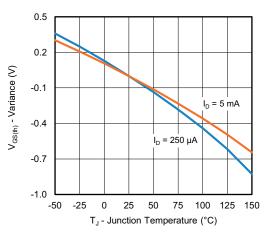




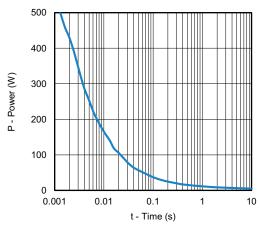
Source-Drain Diode Forward Voltage



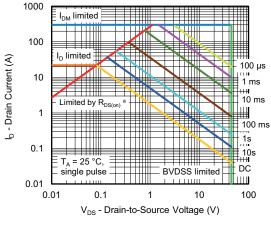
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

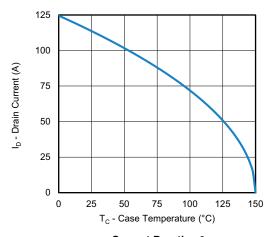


Safe Operating Area

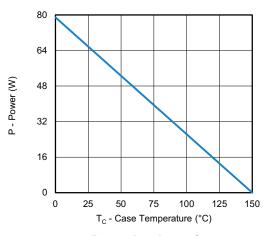
Note

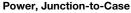
a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

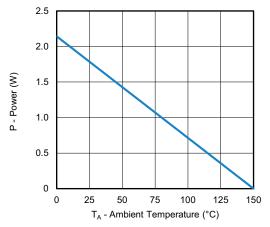




Current Derating a





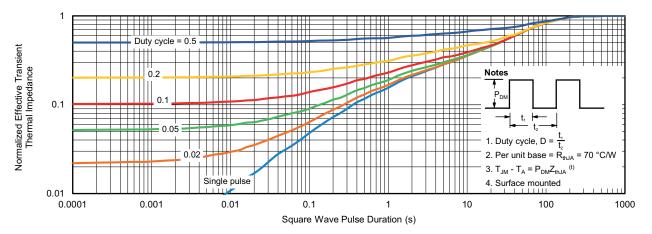


Power, Junction-to-Ambient

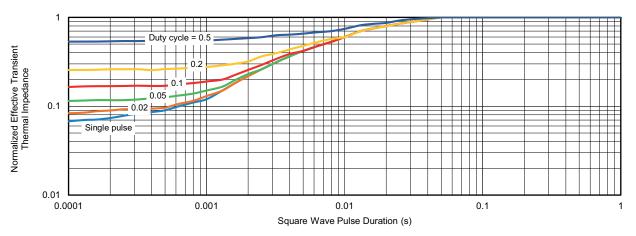
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient

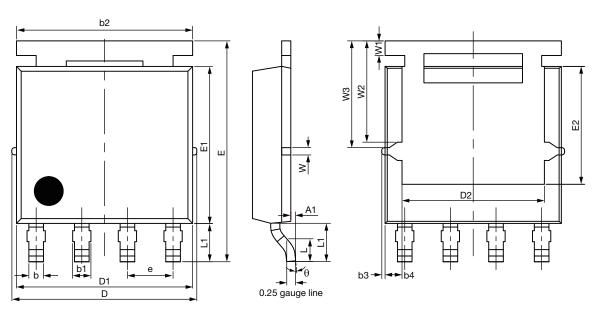


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg263030.

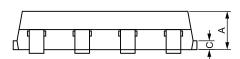


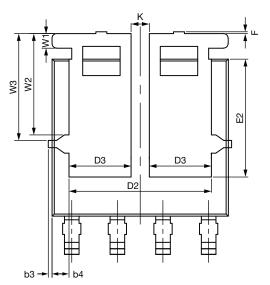
PowerPAK® SO-8L Case Outline 1



Topside view

Backside view (single)





Backside view (dual)



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DIM		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094	•		0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15 6.25 0.238 0.2		0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.133	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W	0.23			0.009			
W1	0.41			0.016			
W2	2.82			0.111			
W3		2.96		0.117			
θ	0°	-	10°	0°	-	10°	

ECN: S19-0643-Rev. E, 05-Aug-2019

DWG: 5976

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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Vishay

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